NPN Triple Diffused Planar Silicon Transistor



2SC3456

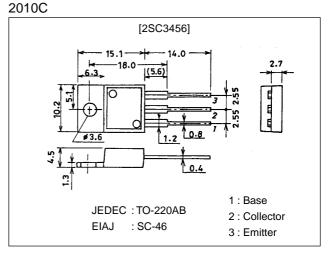
800V/1.5A Switching Regulator Applications

Features

- · High breakdown voltage and high reliability.
- \cdot Fast switching speed (t_f : 0.1 \mu s typ).
- \cdot Wide ASO.
- · Adoption of MBIT process.

Package Dimensions

unit:mm



Specifications

Absolute Maximum Ratings at Ta = 25°C

| Parameter | Symbol | Conditions | Ratings | Unit |
|------------------------------|------------------|--------------------------|-------------|------|
| Collector-to-Base Voltage | V _{CBO} | | 1100 | V |
| Collector-to-Emitter Voltage | VCEO | | 800 | V |
| Emitter-to-Base Voltage | VEBO | | 7 | V |
| Collector Current | IC | | 1.5 | A |
| Collector Current (Pulse) | ICP | PW≤300µs, Duty Cycle≤10% | 5 | A |
| Base Current | Ι _Β | | 0.8 | A |
| Collector Dissipation | PC | Tc=25°C | 40 | W |
| Junction Temperature | Tj | | 150 | °C |
| Storage Temperature | Tstg | | -55 to +150 | °C |

Electrical Characteristics at Ta = 25°C

| Parameter | Symbol | Conditions | Ratings | | | Unit |
|--------------------------|-------------------|--|---------|-----|-----|------|
| | | | min | typ | max | Onit |
| Collector Cutoff Current | ICBO | V _{CB} =800V, I _E =0 | | | 10 | μA |
| Emitter Cutoff Current | IEBO | $V_{EB}=5V, I_{C}=0$ | | | 10 | μA |
| DC Current Gain | hFE1 | V _{CE} =5V, I _C =0.1A | 10* | | 40* | |
| DC Current Gain | h _{FE} 2 | $V_{CE}=5V, I_{C}=0.5A$ | 8 | | | |
| Gain-Bandwidth Product | fT | V _{CE} =10V, I _C =0.1A | | 15 | | MHz |
| Output Capacitance | Cob | V _{CB} =10V, f=1MHz | | 35 | | pF |

*: The h_{FE}1 of the 2SC3456 is classified as follows. When specifying the h_{FE}1 rank, specify two ranks or more in principle.

10 K 20 15 L 30 20 M 40

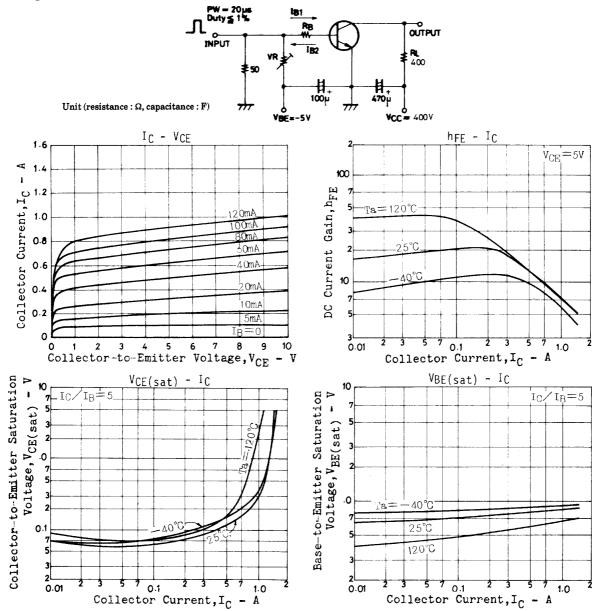
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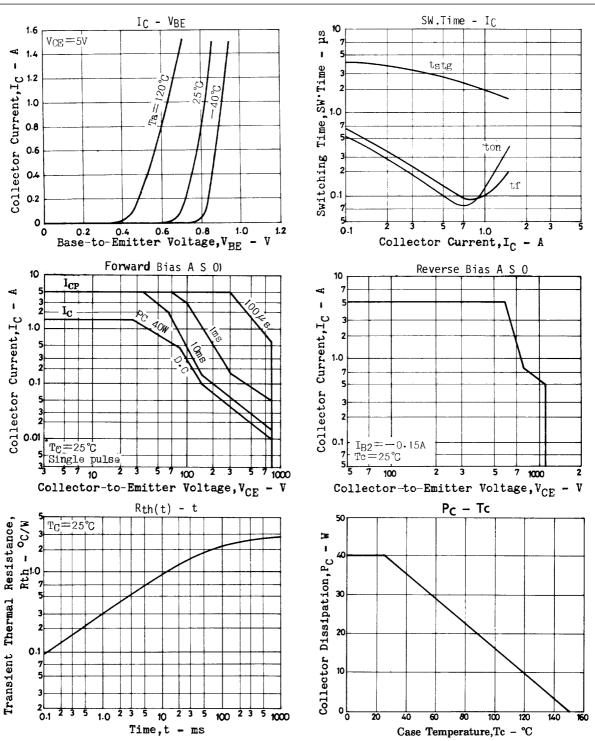
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| Parameter | Symbol | Conditions | Ratings | | | Unit |
|---|-----------------------|---|---------|-----|-----|------|
| | | | min | typ | max | Unit |
| Collector-to-Emitter Saturation Voltage | V _{CE(sat)} | I _C =0.75A, I _B =0.15A | | | 2.0 | V |
| Base-to-Emitter Saturation Voltage | V _{BE(sat)} | I _C =0.75A, I _B =0.15A | | | 1.5 | V |
| Collector-to-Base Breakdown Voltage | V _(BR) CBO | I _C =1mA, I _E =0 | 1100 | | | V |
| Collector-to-Emitter Breakdown Voltage | V(BR)CEO | I _C =5mA, R _{BE} =∞ | 800 | | | V |
| Emitter-to-Base Breakdown Voltage | V(BR)EBO | I _E =1mA, I _C =0 | 7 | | | V |
| Collector-to-Emitter Sustain Voltage | VCEX(sus) | I _C =0.75A, I _{B1} =-I _{B2} =0.15A, L=5mH, clamped | 800 | | | V |
| Turn-ON Time | ton | V _{CC} =400V, 5I _{B1} =-2.5I _{B2} =I _C =1A, R _L =400Ω | | | 0.5 | μs |
| Storage Time | tstg | V _{CC} =400V, 5I _{B1} =-2.5I _{B2} =I _C =1A, R _L =400Ω | | | 3.0 | μs |
| Fall Time | t _f | V_{CC} =400V, 5I _{B1} =-2.5I _{B2} =I _C =1A, R _L =400 Ω | | | 0.3 | μs |

Switching Time Test Circuit





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